

Figure S1. Transfer curves of MoTe₂ Device #1

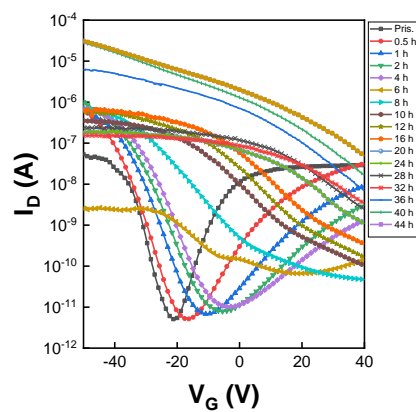


Figure S2. Transfer curves of MoTe₂ Device #2

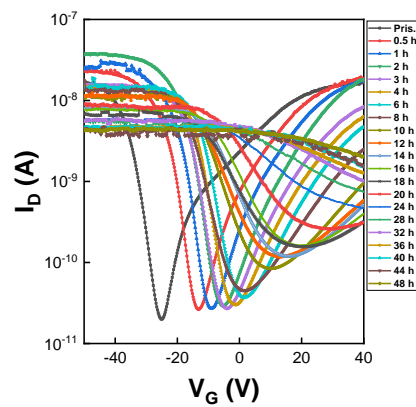


Figure S3. Transfer curves of MoTe₂ Device #3

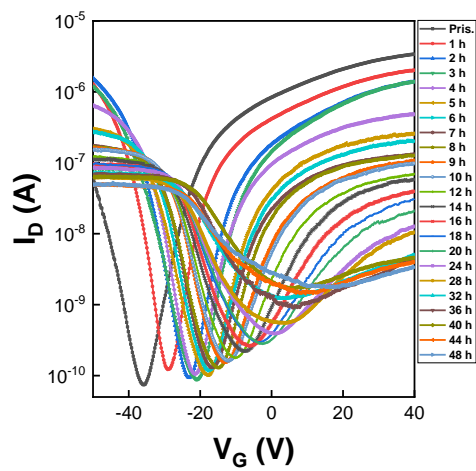


Figure S4. Transfer curves of MoTe₂ Device #4

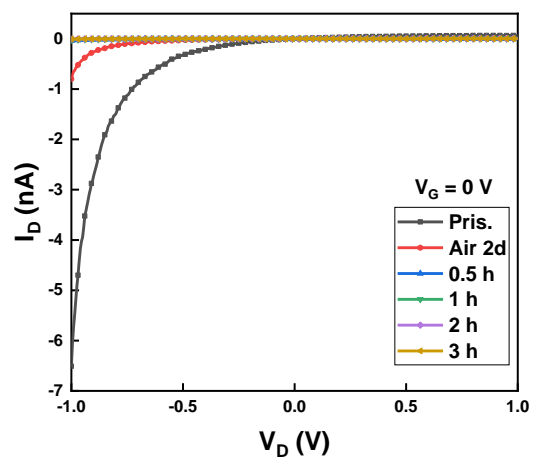


Figure S5. Output curves (I_{ds} - V_{ds}) of Device #1 under zero gate bias

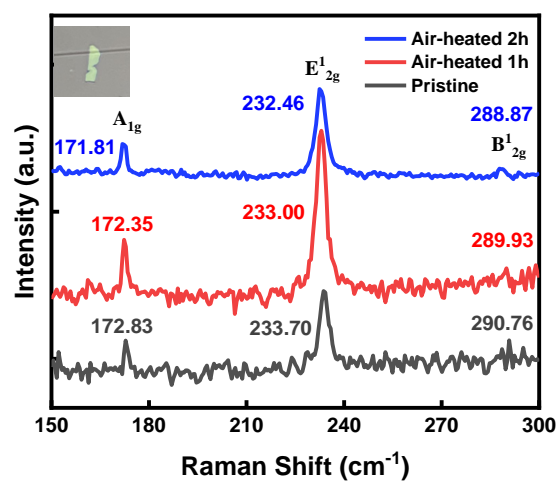


Figure S6. Raman spectra of air-heated MoTe₂ Device #2

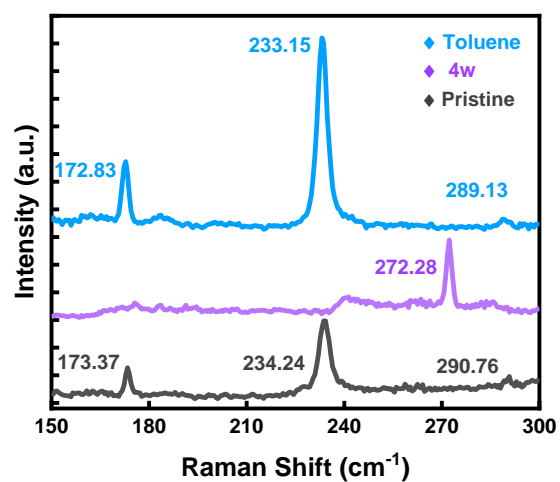


Figure S7. Raman spectra of toluene treated, air-exposed MoTe₂ flake

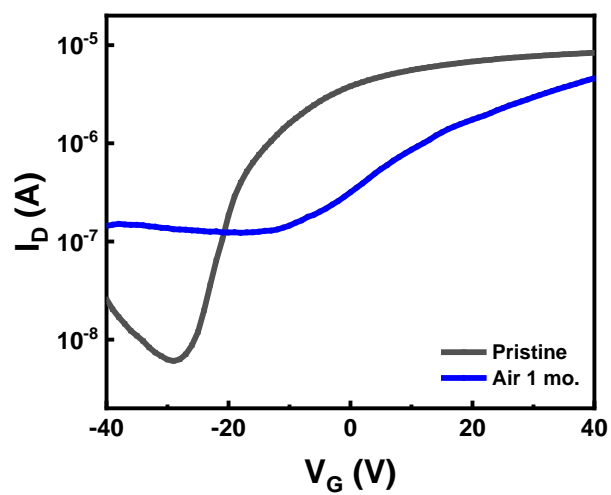


Figure S8. Transfer Characteristics curves of as-fabricated (dark grey) and air-exposed for 1-month (blue) MoTe₂ FET

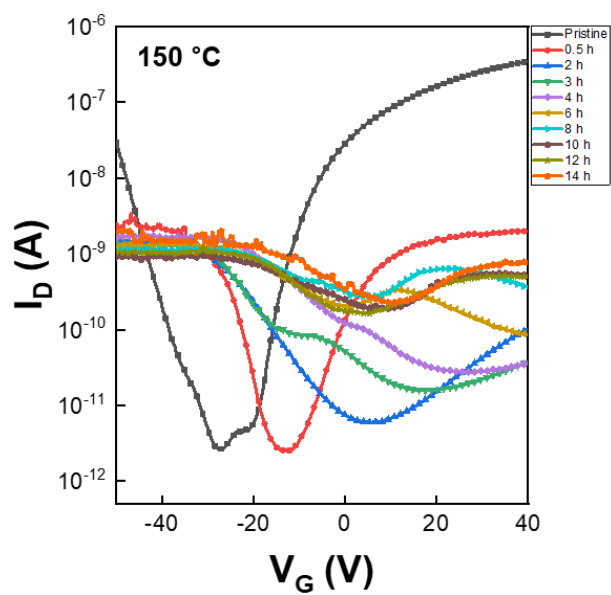


Figure S9. Transfer Characteristics curves of MoTe₂ FET air heated at 150 °C

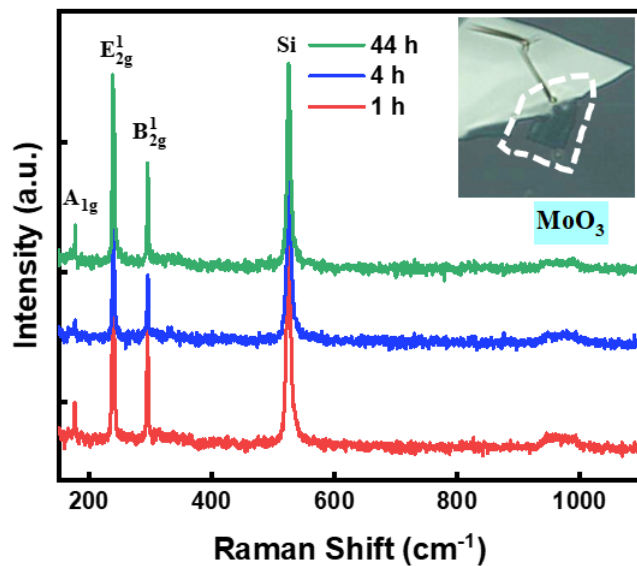


Figure S10. Raman Spectra of air heated MoTe₂ flake over a range 150 – 1100 cm⁻¹ (inset: optic image)

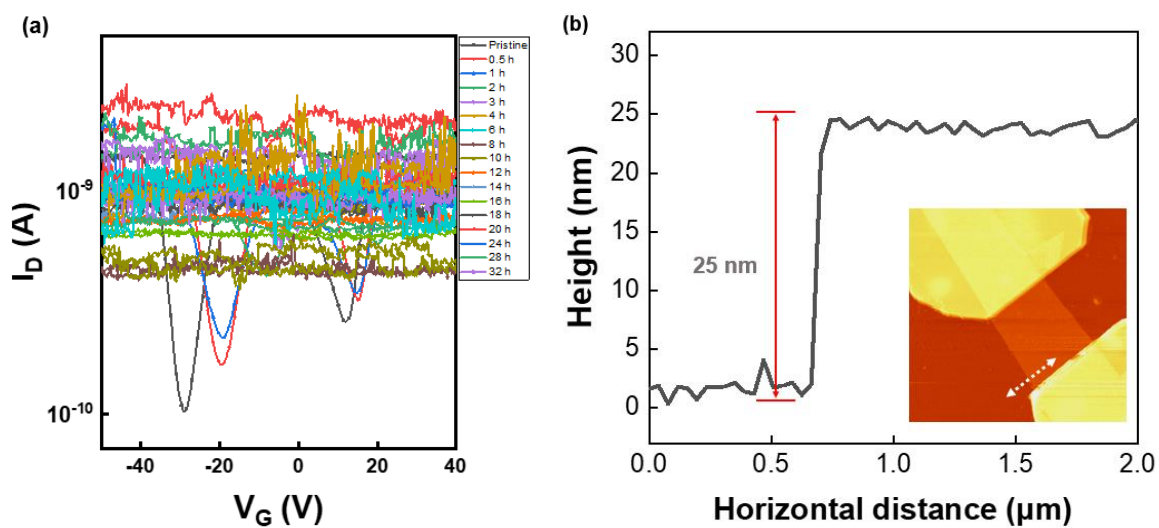


Figure S11. (a) Transfer curves and (b) AFM height profile (inset: AFM image) of MoTe₂ FET #5